

Supporting Information

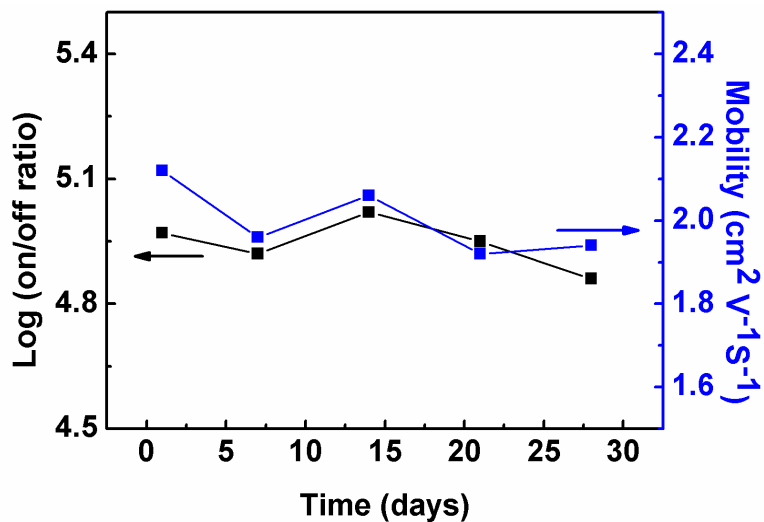


Figure S1. The stability of printed SCNT TFT device fabricated on SiO_2/Si substrates.

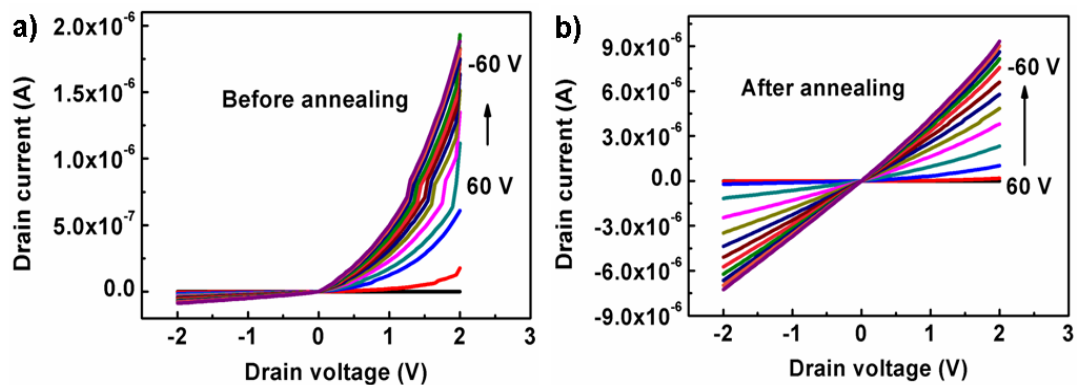


Figure S2. Typical output curve for the printed TFTs based on chemically functionalized CoMoCat 76 before and after annealing at 150°C for 30 min.

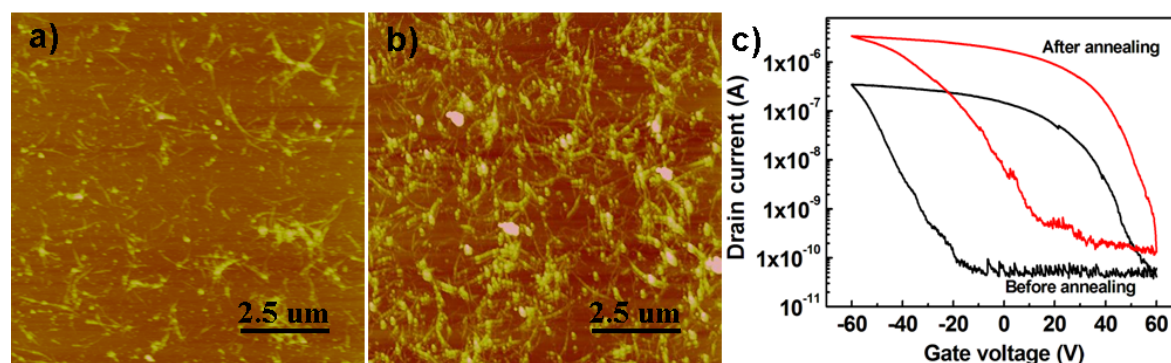


Figure S3. Typical AFM images of printed SCNT thin films and transfer curves of the printed SCNT TFTs before and after annealing at 200 °C for 30 min (using ink 4 or ink 5 as the printing inks.). As shown in figure S2, PVP can be effectively eliminated after annealing at 200 °C for 30 min, and the electrical properties of the printed TFTs were enhanced.

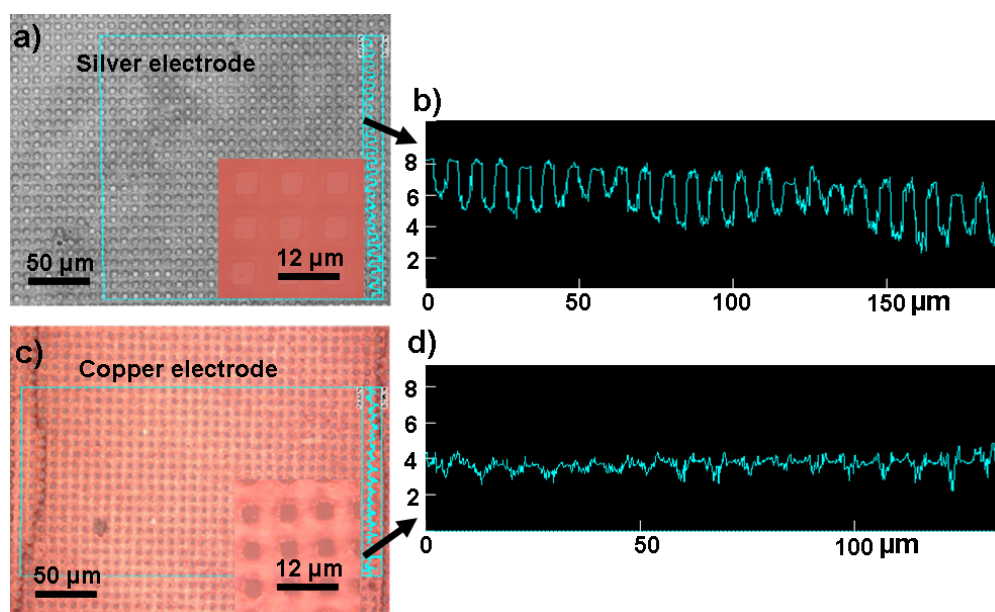


Figure S4. Optical images and the height changes of silver electrodes (a, b) before and (c, d) after electroless deposition of copper for 50 min. As shown in figure S3, the surface roughness is decreased after electroless deposition of copper. The insets in figure 3Sa and 3Sc are the enlarged optical images of silver and copper electrode patterns, respectively.

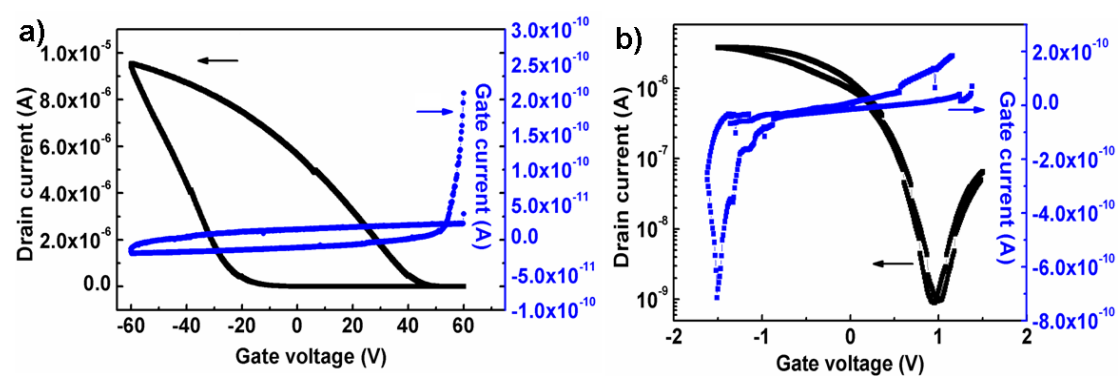


Figure S5. Typical I_d (drain current)- V_g (gate current) and I_g (gate current)- V_g curves of the printed bottom-gate SCNTs fabricated on SiO_2/Si substrates and all-printed SCNT TFTs on the flexible substrates.